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Front Matter: Volume 7028

, "Front Matter: Volume 7028," Proc. SPIE 7028, Photomask and Next-Generation Lithography Mask Technology XV, 702801 (27 May 2008); doi: 10.1117/12.801299

SPIE.

Event: Photomask and NGL Mask Technology XV, 2008, Yokohama, Japan

PROCEEDINGS OF SPIE

Photomask and Next-Generation Lithography Mask Technology XV

Toshiyuki Horiuchi
Editor

**16–18 April 2008
Yokohama, Japan**

Sponsored by
PMJ—Photomask Japan
BACUS—The international technical group of SPIE dedicated to the advancement of
photomask technology
SPIE

Published by
SPIE

Part One of Two Parts

Volume 7028

Proceedings of SPIE, 0277-786X, v. 7028

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Author(s), "Title of Paper," in *Photomask and Next-Generation Lithography Mask Technology XV*, edited by Toshiyuki Horiuchi, Proceedings of SPIE Vol. 7028 (SPIE, Bellingham, WA, 2008) Article CID Number.

ISSN 0277-786X
ISBN 9780819472434

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
SPIE.org

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Contents

Part One

xv	<i>Symposium Committees</i>
xvii	<i>Conference Committee</i>

MATERIAL FOR PHOTOMASK

7028 02	Logic device scaling trend in ITRS 2007 (Invited Paper) [7028-01] K. Imai, NEC Electronics Corp. (Japan)
7028 03	MoSi absorber photomask for 32nm node (Invited Paper) [7028-02] T. Konishi, Y. Kojima, H. Takahashi, M. Tanabe, T. Haraguchi, M. Lamantia, Y. Fukushima, Y. Okuda, Toppan Printing Co., Ltd. (Japan)
7028 04	The ultimate chrome absorber in photomask making [7028-03] M. Hashimoto, H. Iwashita, A. Kominato, H. Shishido, M. Ushida, H. Mitsui, HOYA Corp. (Japan)
7028 05	Photomask technology for 32nm node and beyond [7028-04] R. Hikichi, H. Ishii, H. Migita, N. Kakehi, M. Shimizu, H. Takamizawa, T. Nagano, Dai Nippon Printing Co., Ltd. (Japan); M. Hashimoto, H. Iwashita, T. Suzuki, M. Hosoya, Y. Ohkubo, M. Ushida, H. Mitsui, HOYA Corp. (Japan)

PHOTOMASK PROCESS TECHNOLOGY

7028 07	Phase shift mask etch process development utilizing a scatterometry-based metrology tool [7028-06] J. Plumhoff, Oerlikon USA, Inc. (USA); A. Gray, Univ. of California, Davis (USA) and n&k Technology, Inc. (USA)
7028 08	Advanced damage-free photomask cleaning for 45/32nm technology nodes [7028-07] R. Gouk, J. Jeon, F. Li, J. Papanu, B. Wu, R. Yalamanchili, Applied Materials (USA)
7028 09	Application of two-fluid nozzles for advanced photomask cleaning process [7028-08] K. Masui, T. Takemoto, K. Otsubo, M. Sakai, T. Higaki, H. Watanabe, Toshiba Corp. (Japan); T. Kikuchi, Y. Kurokawa, Shibaura Mechatronics Corp. (Japan)

WRITING TECHNOLOGY

7028 0A	Linewidth roughness characterization in step and flash imprint lithography (Invited Paper) [7028-09] G. M. Schmid, N. Khusnatdinov, C. B. Brooks, D. LaBrake, E. Thompson, D. J. Resnick, Molecular Imprints, Inc. (USA)
---------	--

- 7028 0B **Multi column cell (MCC) e-beam exposure system for mask writing** [7028-10]
H. Yasuda, A. Yamada, M. Yamabe, Association of Super-Advanced Electronics Technologies (Japan)
- 7028 0C **Modeling of charging effect and its correction by EB mask writer EBM-6000** [7028-11]
N. Nakayamada, S. Wake, T. Kamikubo, H. Sunaoshi, S. Tamamushi, NuFlare Technology, Inc. (Japan)
- 7028 0D **Mask image position correction for double patterning lithography** [7028-12]
M. Saito, M. Itoh, O. Ikenaga, K. Ishigo, Toshiba Corp. (Japan)
- 7028 0E **Distributed processing (DP) based e-beam lithography simulation with long range correction algorithm in e-beam machine** [7028-13]
W.-T. Ki, J.-H. Choi, B.-G. Kim, S.-G. Woo, H.-K. Cho, Samsung Electronics Co., Ltd. (South Korea)

MDP

- 7028 0F **Case study: the impact of VSB fracturing** [7028-14]
B. Dillon, Photronics Inc. (USA); T. Norris, MP Mask Technology Ctr., LLC (USA)
- 7028 0G **Model based short range mask process correction** [7028-15]
G. Chen, J.-S. Wang, S. Bai, R. Howell, J. Wiley, A. Vacca, Brion Technologies, Inc. (USA); T. Kurosawa, T. Nishibe, T. Takigawa, Brion Technologies KK (Japan)

NGL I

- 7028 0I **Selete EUV reticle shipping and storage test results** [7028-17]
K. Ota, M. Amemiya, T. Taguchi, O. Suga, MIRAI-Semiconductor Leading Edge Technologies, Inc. (Japan)
- 7028 0J **Damage analysis of EUV mask under Ga focused ion beam irradiation** [7028-18]
Y. Nishiyama, T. Amano, H. Shigemura, T. Terasawa, O. Suga, MIRAI-Semiconductor Leading Edge Technologies, Inc. (Japan); T. Kozakai, S. Kikuchi, K. Shiina, A. Yasaka, R. Hagiwara, SII NanoTechnology Inc. (Japan)

EDA AND DFM FOR PHOTOMASK I

- 7028 0L **Hybrid resist model to enhance continuous process window model for OPC** [7028-20]
Q. Zhang, K. Lucas, Synopsys, Inc. (USA)
- 7028 0M **Predictive modeling of lithography-induced linewidth variation** [7028-21]
A. B. Kahng, S. V. Muddu, Univ. of California, San Diego (USA)
- 7028 0N **OPC model enhancement using parameter sensitivity methodology** [7028-22]
B. S. Ward, Synopsys, Inc. (Belgium); M. Drapeau, Synopsys, Inc. (Canada)

- 7028 0O **Yield-centric layout optimization with precise quantification of lithographic yield loss** [7028-23]
S. Kobayashi, S. Kyoh, K. Kinoshita, Y. Urakawa, E. Morifuji, Toshiba Corp. (Japan);
S. Kuramoto, Takumi Technology KK (Japan); S. Inoue, Toshiba Corp. (Japan)

NGL II

- 7028 0P **Metrology of EUV masks by EUV-scatterometry and finite element analysis** [7028-24]
J. Pomplun, S. Burger, F. Schmidt, Zuse Institute Berlin (Germany) and JCMwave GmbH (Germany); F. Scholze, C. Laubis, Physikalisch-Technische Bundesanstalt (Germany);
U. Dersch, Advanced Mask Technology Ctr. GmbH & Co. KG (Germany)
- 7028 0R **32 nm imprint masks using variable shape beam pattern generators** [7028-26]
K. Selinidis, E. Thompson, G. Schmid, N. Stacey, J. Perez, J. Maltabes, D. J. Resnick, Molecular Imprints, Inc. (USA); J. Yeo, H. Kim, B. Eynon, Samsung Electronics Co., Ltd. (South Korea)

EDA AND DFM FOR PHOTOMASK II

- 7028 0S **Describing litho-constrained layout by a high-resolution model filter** [7028-27]
M.-C. Tsai, Synopsys, Inc. (USA)
- 7028 0T **Source optimization and mask design to minimize MEEF in low k_1 lithography** [7028-28]
G. Xiao, T. Cecil, L. Pang, B. Gleason, J. McCarty, Luminescent Technologies, Inc. (USA)
- 7028 0U **Model-based mask verification on critical 45nm logic masks** [7028-29]
F. Sundermann, F. Foussadier, STMicroelectronics (France); T. Takigawa, J. Wiley, A. Vacca, L. Depre, G. Chen, S. Bai, J.-S. Wang, R. Howell, V. Arnoux, Brion Technologies (USA);
K. Hayano, S. Narukawa, S. Kawashima, H. Mohri, N. Hayashi, H. Miyashita, Dai Nippon Printing Co. (Japan); Y. Trouiller, CEA/LETI (France); F. Robert, F. Vautrin, G. Kerrien, J. Planchot, C. Martinelli, STMicroelectronics (France); J. L. Di-Maria, CEA/LETI (France);
V. Farys, B. Vandewalle, STMicroelectronics (France); L. Perraud, CEA/LETI (France);
J. C. Le Denmat, A. Villaret, C. Gardin, E. Yesilada, M. Saied, STMicroelectronics (France)

OPC AND LITHOGRAPHY TECHNOLOGIES I

- 7028 0V **Optimization of MDP, mask writing, and mask inspection for mask manufacturing cost reduction (Invited Paper)** [7028-30]
M. Yamabe, Association of Super-Advanced Electronics Technologies (Japan)
- 7028 0W **Scanner fleet management utilizing programmed hotspot patterns** [7028-31]
K. Yoshida, S. Inoue, K. Hashimoto, S. Tanaka, M. Satake, T. Obara, K. Takahata, E. Yamanaka, M. Kariya, H. Morinaga, S. Mimotogi, Toshiba Corp. (Japan)

- 7028 0X **Separable OPC models for computational lithography** [7028-32]
H.-Y. Liu, Q. Zhao, J. F. Chen, J. Jiang, Brion Technologies, Inc. (USA); R. Socha, ASML Technology Development Ctr. (USA); E. Van Setten, A. Engelen, J. Meessen, ASML Netherlands B.V. (Netherlands); M. M. Crouse, ASML Albany (USA); M. Feng, W. Shao, H. Cao, Y. Cao, Brion Technologies, Inc. (USA); L. Van Look, J. Bekaert, G. Vandenberghe, IMEC vzw (Belgium); J. Finders, ASML Netherlands B.V. (Netherlands)
- 7028 0Y **AF fixer: new incremental OPC method for optimizing assist feature** [7028-33]
S.-G. Jung, S.-W. Kim, S.-W. Suh, Y.-C. Kim, S.-J. Lee, S.-W. Choi, W.-S. Han, J.-T. Moon, Samsung Electronics Co., Ltd. (South Korea); L. D. Barnes, X. Li, R. M. Lugg, S. Lee, K. Koo, M. Do, F. P. Amoroso, B. Painter, Synopsys, Inc. (USA)
- 7028 0Z **Extension of the 2D-TCC technique to optimize mask pattern layouts** [7028-34]
M. Hakko, K. Yamazoe, M. Kawashima, Y. Sekine, M. Ohta, T. Honda, Canon Inc. (Japan)

OPC AND LITHOGRAPHY TECHNOLOGIES II

- 7028 10 **The lithography technology for the 32 nm HP and beyond (Invited Paper)** [7028-35]
M. Dusa, ASML TDC USA (USA); B. Arnold, ASML TDC (USA); J. Finders, H. Meiling, K. van Ingen Schenau, ASML (Netherlands); A. C. Chen, ASML TDC Asia (Taiwan)
- 7028 11 **Model-based SRAF insertion through pixel-based mask optimization at 32nm and beyond** [7028-36]
K. Sakajiri, A. Trichtkov, Y. Granik, Mentor Graphics Corp. (USA)
- 7028 12 **A study of mask specification in spacer patterning technology** [7028-132]
H. Mukai, Y. Kobayashi, S. Yamaguchi, K. Kawano, K. Hashimoto, Toshiba Corp. (Japan)
- 7028 13 **Rigorous vectorial modeling for polarized illumination and projection pupil in OPC** [7028-37]
Q. Zhang, H. Song, K. Lucas, Synopsys, Inc. (USA); B. Ward, Synopsys, Inc. (Belgium); J. Shiely, Synopsys, Inc. (USA)
- 7028 14 **Impact of patterning strategy on mask fabrication beyond 32nm** [7028-38]
S. Mimotogi, T. Higaki, H. Kanai, S. Tanaka, M. Satake, Y. Kitamura, K. Koderia, K. Ishigo, T. Kono, M. Asano, K. Takahata, S. Inoue, Toshiba Corp. (Japan)
- 7028 15 **Mask transmission resonance in bi-layer masks** [7028-39]
V. Philipsen, P. De Bisschop, IMEC (Belgium); K. Mesuda, IMEC (Belgium) and Dai Nippon Printing Co., Ltd. (Japan)

PROGRESSIVE DEFECT (HAZE)

- 7028 16 **ACLV degradation: root cause analysis and effective monitoring strategy** [7028-40]
A. Tchikoulaeva, A. Holfeld, AMD Saxony LLC & Co. KG (Germany); M. Arend, E. Foca, Advanced Mask Technology Ctr. GmbH & Co. KG (Germany)
- 7028 17 **Printability impact of progressive defects: ammonium sulfate emulation study** [7028-41]
B. Grenon, Grenon Consulting Inc. (USA); T. Huang, A. Dayal, K. Bhattacharyya, KLA-Tencor Corp. (USA)
- 7028 18 **Prevention of chemical residue from growing into Haze defect on PSM pattern edge after**

normal cleaning process [7028-42]

J. Choi, J. Jung, H. Lee, J. Oh, S. Kang, H. Jeong, Y. Kim, H. Cho, Samsung Electronics Co., Ltd. (South Korea)

REPAIRING TECHNOLOGY

7028 1A **Nanomachining processes for 45, 32 nm node mask repair and beyond [7028-45]**
T. Robinson, A. Dinsdale, R. Bozak, R. White, M. Archuleta, RAVE LLC (USA)

7028 1C **Mask CD control (CDC) using AIMS as the CD metrology data source [7028-47]**
G. Ben-Zvi, E. Zait, V. Dmitriev, S. Labovitz, E. Graitzer, Pixar Technology (Israel); K. Böhm, R. Birkner, T. Scheruebl, Carl Zeiss SMS GmbH (Germany)

INSPECTION TECHNOLOGY

7028 1E **"What you see is what you print": aerial imaging as an optimal discriminator between printing and non-printing photomask defects [7028-49]**
A. Sagiv, S. Mangan, Applied Materials (Israel)

7028 1F **A novel approach: high resolution inspection with wafer plane defect detection [7028-50]**
C. Hess, M. Wihl, R. Shi, Y. Xiong, S. Pang, KLA-Tencor Corp. (USA)

7028 1G **Practical application of aerial imaging mask inspection for memory devices [7028-51]**
H. J. Baik, D. H. Chung, Y. H. Kim, H. K. Cho, Samsung Electronics Co., Ltd. (South Korea); A. Sagiv, S. Mangan, Z. Parizat, E. Y. Park, Y. Bami, D. Bernstein, Applied Materials (Israel)

7028 1H **Wafer plane inspection for advanced reticle defects [7028-52]**
R. Nagpal, F. Ghadiali, J. Kim, Intel Corp. (USA); T. Huang, S. Pang, KLA-Tencor Corp. (USA)

7028 1I **Resist pattern inspection function for LM7500 reticle inspection system [7028-53]**
H. Moribe, Y. Kato, K. Nakamura, T. Bashomatsu, NEC Corp. (Japan); T. Igeta, NEC Control Systems, Ltd. (Japan); K. Ogiwara, T. Okada, DNP Fine Electronics Sagamihara Co., Ltd. (Japan)

7028 1J **Fast integrated die-to-die transmitted, reflected and STARlight-2 defect inspection on memory masks [7028-54]**
A. Lan, J. Hsu, Inotera Memory Inc. (Taiwan); S. Chakravarty, V. Hsu, E. Chen, E. Lu, J. Miller, KLA-Tencor Corp. (USA)

METROLOGY FOR PHOTOMASK

7028 1K **IntenCD: an application for CD uniformity mapping of photomask and process control at maskshops [7028-55]**
H. Kim, M. Lee, S. Lee, Y.-S. Sung, B. Kim, S.-G. Woo, H. Cho, Samsung Electronics Co., Ltd. (South Korea); M. B. Yishai, L. Shoval, C. Couderc, Applied Materials (Israel)

- 7028 1L **Controlling phase induced CD non-uniformity effects of PSM photo-masks** [7028-56]
D. Rost, Mask Technology Ctr., LLC (USA); M. Ben-Yishai, L. Shoval, C. Couderc, Applied Materials (Israel)
- 7028 1M **Mask CD compensation method using diffraction intensity for lithography equivalent metrology** [7028-57]
T. Nagai, T. Sutou, Y. Inazuki, H. Hashimoto, Dai Nippon Printing Co., Ltd. (Japan); N. Toyama, DNP Corp. USA (USA); Y. Morikawa, H. Mohri, N. Hayashi, Dai Nippon Printing Co., Ltd. (Japan)
- 7028 1N **Reliable measurement method for complicated OPC pattern** [7028-58]
T. Aihara, Toppan Printing Co., Ltd. (Japan); S. Kondo, Toppan Electronics Inc. (USA); M. Higuchi, Toppan Printing Co., Ltd. (Japan)
- 7028 1O **The study to optimize CD uniformity by reliable area CD measurement on 45nm D/R DRAM** [7028-59]
Y. Choi, S. Oh, M. Kim, Y. Kim, C. Kim, Hynix Semiconductor (South Korea)

COST AND STRATEGY ON PHOTOMASK

- 7028 1P **Mask and wafer cost of ownership (COO) from 65 to 22 nm half-pitch nodes** [7028-60]
G. Hughes, L. C. Litt, A. Wüest, S. Palaiyanur, SEMATECH (USA)

Part Two

POSTER SESSION 5A: NGL

- 7028 1Q **EUV mask process development status for full field EUV exposure tool** [7028-61]
T. Abe, T. Adachi, H. Akizuki, H. Mohri, N. Hayashi, Dai Nippon Printing Co., Ltd. (Japan); K. Ishikiriyama, Intel Corp. (Japan)
- 7028 1R **Effects of mask absorber thickness on printability in EUV lithography with high resolution resist** [7028-62]
T. Kamo, H. Aoyama, T. Tanaka, O. Suga, MIRAI-Semiconductor Leading Edge Technologies, Inc. (Japan)
- 7028 1S **Impact of mask blank and mirror surface roughness on actinic EUVL mask blank inspection signal** [7028-63]
T. Yamane, T. Tanaka, T. Terasawa, O. Suga, MIRAI-Semiconductor Leading Edge Technologies, Inc. (Japan); T. Tomie, National Institute of Advanced Industrial Science and Technology (Japan)
- 7028 1T **Evaluation of defect repair of EUVL mask pattern using FIB-GAE method** [7028-64]
T. Amano, Y. Nishiyama, H. Shigemura, T. Terasawa, O. Suga, MIRAI-Semiconductor Leading Edge Technologies, Inc. (Japan); R. Hagiwara, K. Shiina, S. Kikuchi, A. Yasaka, SII NanoTechnology, Inc. (Japan)
- 7028 1U **The source of carbon contamination for EUV mask production** [7028-129]
Y. Kim, J. Lee, Y. Choi, C. Kim, Hynix Semiconductor Inc. (South Korea)

7028 1V **Optimization of measuring conditions for templates of UV nano imprint lithography** [7028-65]
K. Yoshida, K. Kojima, M. Abe, S. Sasaki, M. Kurihara, Y. Morikawa, H. Mohri, N. Hayashi, Dai Nippon Printing Co., Ltd. (Japan)

7028 1W **UV-NIL mask making and imprint evaluation** [7028-66]
A. Fujii, Y. Sakai, J. Mizuochi, T. Hiraka, S. Yusa, K. Kuriyama, M. Sakaki, T. Sutou, S. Sasaki, Y. Morikawa, H. Mohri, N. Hayashi, Dai Nippon Printing Co., Ltd. (Japan)

POSTER SESSION 5B: WRITING TECHNOLOGY

7028 1X **Image placement error of photomask due to pattern loading effect: analysis and correction technique for sub-45 nm node** [7028-67]
J. Choi, S. H. Lee, D. Nam, B. G. Kim, S.-G. Woo, H. K. Cho, Samsung Electronics Co., Ltd. (South Korea)

7028 1Y **Improvement of position accuracy in mask-writing electron beam lithography with a multi-pass writing strategy for reducing position errors due to resist charging** [7028-68]
N. Kobayashi, K. Goto, T. Wakatsuki, JEOL Ltd. (Japan); T. Komagata, JEOL USA, Inc. (USA); Y. Nakagawa, JEOL Ltd. (Japan)

7028 1Z **Evaluation of TF11 attenuated-PSM mask blanks with DUV laser patterning** [7028-69]
K. Xing, C. Björnberg, H. Karlsson, A. Paulsson, P. Beiming, J. Vedenpää, J. Walford, Micronic Laser Systems AB (Sweden)

POSTER SESSION 5C: PROCESS TECHNOLOGY

7028 23 **In-situ chamber clean for chromium etch application** [7028-72]
Z. Mao, X. Chen, D. Knick, M. Grimbergen, M. Chandrahod, I. Ibrahim, A. Kumar, Applied Materials (USA)

7028 24 **Patterning capability and limitations by pattern collapse in 45nm and below node photo mask production** [7028-73]
G.-H. Hwang, M. Patil, S.-K. Seo, C.-B. Yu, I.-B. Hur, D. H. Kim, C. Shin, PKL Co., Ltd. (South Korea); S.-M. Jung, Y.-H. Lee, Kyungpook National Univ. (South Korea); S.-S. Choi, PKL Co., Ltd. (South Korea)

7028 25 **A modified dynamical model of drying process of polymer blend solution coated on a flat substrate** [7028-74]
H. Kagami, Nagoya College (Japan)

7028 26 **A N₂/CDA reticle purging approach with enhanced efficiency** [7028-75]
C.-W. Ku, National Taipei Univ. of Technology (Taiwan); W.-J. Tseng, RexChip Electronics Corp. (Taiwan); P.-S. Lee, Gudeng Precision Industrial Co., Ltd. (Taiwan); S.-C. Hu, National Taipei Univ. of Technology (Taiwan)

7028 28 **Very high sensitivity mask transmittance mapping and measurements based on non imaging optics with Galileo** [7028-77]
G. Ben-Zvi, V. Dmitriev, E. Graitzer, E. Zait, O. Sharoni, S. Labovitz, Pixar Technology (Israel)

POSTER SESSION 5D: PROGRESSIVE DEFECT (HAZE)

- 7028 29 **Novel model of haze generation on photomask** [7028-78]
H. Akutsu, S. Yamaguchi, K. Otsubo, M. Tamaoki, A. Shimazaki, R. Yoshimura, F. Aiga, T. Tada, Toshiba Corp. (Japan)
- 7028 2B **An explosive haze formation under low energy exposure** [7028-80]
J. Lee, Y. Kim, Y. Choi, C. Kim, Hynix Semiconductor Inc. (South Korea)
- 7028 2C **Post cleaned surface modification treatment to prevent near pellicle haze generation in sulfate free cleaned ArF EAPSM** [7028-81]
M. Patil, J.-M. Kim, PKL, Ltd. (South Korea); S.-M. Jung, PKL, Ltd. (South Korea) and Kyungpook National Univ. (South Korea); I.-B. Hur, S.-S. Choi, PKL, Ltd. (South Korea); Y. H. Lee, Kyungpook National Univ. (South Korea)
- 7028 2D **Implementation of new reticle inspection technology for progressive mask defect detection strategy in wafer fabs** [7028-82]
C. Liu, A. Lu, C. Wang, E. Guo, Semiconductor Manufacturing International Corp. (China); D. Fan, L. Yun, KLA-Tencor Corp. (China); S. Liu, R. Badoni, E. Lu, KLA-Tencor Corp. (USA)
- 7028 2E **A study of high peroxydinitrate generated in purge head outlet of charger with continuous supply of superior purification CDA system for 193 nm ArF reticle haze prevention** [7028-83]
F.-S. Chu, S.-H. Chiou, Rexchip Electronics Corp. (Taiwan)
- 7028 2F **Haze acceleration system for photo mask application by using high repetition ArF excimer laser** [7028-84]
D.-J. Kim, H.-J. Kim, S.-H. Eom, K.-J. Lee, W.-K. Cho, S.-H. Chung, Kornic Systems Corp. (South Korea)
- 7028 2G **A practical solution to the critical problem of 193 nm reticle haze** [7028-130]
D. L. Halbmaier, Y. Ohyashiki, O. Kishkovich, Entegris, Inc. (USA)
- 7028 2H **Validation of ArF PSM quality using AIMS simulation method in repeated cleaning** [7028-44]
D.-S. Lee, H.-J. Jung, J.-K. Lee, W.-G. Jung, D.-H. Lee, C. Shin, S.-S. Choi, M.-H. Choi, PKL Co., Ltd. (South Korea)

POSTER SESSION 5E: INSPECTION

- 7028 2I **Die-to-database mask inspection with variable sensitivity** [7028-85]
H. Tsuchiya, M. Tokita, T. Nomura, T. Inoue, Association of Super-Advanced Electronics Technologies (Japan)
- 7028 2J **Thin-line de-sense capability for database mode inspections with KLA-Tencor TeraScanHR** [7028-86]
A. Goonesekera, I. Lee, B. Mu, A. Dayal, KLA-Tencor Corp. (USA)
- 7028 2K **Improvement of image quality and inspection speed in LM7500 reticle inspection system** [7028-87]
H. Moribe, T. Bashomatsu, K. Matsumura, NEC Corp. (Japan); A. Uehara, H. Takahashi, NEC Control Systems, Ltd. (Japan)

- 7028 2L **Results of new CD detection capability on advanced reticles** [7028-88]
A. Goonesekera, H. Schmalfuss, I. Lee, C. Guan, A. Dayal, KLA-Tencor Corp. (USA);
T. Schulmeyer, J. Heumann, Advanced Mask Technology Ctr. (Germany)
- 7028 2M **Comparison of TeraStar SL1, TeraScanHR DDR, DDT and SL2 to identify an efficient mask re-qualification inspection mode for 7Xnm half pitch design node production reticles in advanced memory wafer fab** [7028-89]
K. Kaneko, T. Kobayashi, Elpida Memory, Inc. (Japan); J. Zhu, N. Takatsu, P. Yu, K. Ito, T. Kojima, Y. Nagaoka, KLA-Tencor Corp. (USA)
- 7028 2N **Results of new mask contamination inspection capability STARlight2+ 72nm pixel for qualifying memory masks in wafer fabs** [7028-90]
R. Dover, J. Zhu, N. Schmidt, M. Lang, KLA-Tencor Corp. (USA)
- 7028 2O **Improving COO on KLA-Tencor wafer fab reticle inspections by implementing pixel migration as new STARlight2+ capability** [7028-91]
S. M. Yen, United Microelectronics Corp. (Taiwan); S. Chakravarty, J. Huang, J. Miller, R. Dover, D. Wang, KLA-Tencor Corp. (USA)
- 7028 2P **Inspectability of PSM masks for the 32nm node using STARlight2+** [7028-92]
C.-T. Huang, Y.-F. Cheng, S.-M. Kuo, C.-H. Huang, United Microelectronics Corp. (Taiwan); S. Chakravarty, J. Huang, J. Lin, D. Wang, KLA-Tencor Corp. (USA)
- 7028 2Q **Qualification of aerial image 193nm inspection tool for all masks and all process steps** [7028-93]
D. Rost, R. Mann, R. Gardner, MP - Mask Technology Ctr., LLC (USA); D. Bernstein, D. Olvera, S. Kurin, C. Couderc, Applied Materials (Israel)
- 7028 2R **The study of defect inspection with die to model based on aerial image** [7028-94]
S. Kunitani, A. Kobayashi, S. Nagashige, Toppan Printing Co., Ltd. (Japan)

POSTER SESSION 5F: METROLOGY FOR PHOTOMASK

- 7028 2S **Increasing the predictability of AIMS measurements by coupling to resist simulations** [7028-95]
B. Meliorisz, Friedrich-Alexander Univ. Erlangen-Nuremberg (Germany) and Fraunhofer-Institute of Integrated Systems and Device Technology (Germany); A. Erdmann, T. Schnattinger, Fraunhofer-Institute of Integrated Systems and Device Technology (Germany); U. Strößner, T. Scherübl, Carl Zeiss SMS GmbH (Germany); P. De Bisschop, V. Philipsen, IMEC (Belgium)
- 7028 2T **Surface energy control techniques for photomask fabrication and their characterizations with scanning probe microscopy** [7028-96]
M. Kurihara, S. Hatakeyama, K. Yoshida, M. Abe, D. Totsukawa, Y. Morikawa, H. Mohri, N. Hayashi, Dai Nippon Printing Co., Ltd. (Japan)
- 7028 2U **Hotspot management in which mask fabrication errors are considered** [7028-97]
M. Kariya, E. Yamanaka, K. Yoshida, K. Konomi, M. Satake, S. Tanaka, Toshiba Corp. (Japan)

- 7028 2V **The verification of printability about marginal defects and the detectability at the inspection tool in sub 50nm node** [7028-98]
H. Lee, G. Jeong, K. Seo, S. Kim, C. Kim, Hynix Semiconductor Inc. (South Korea)
- 7028 2W **Wafer level CD metrology on photomasks using aerial imaging technology** [7028-99]
T. Scherübl, U. Ströbner, H. Seitz, R. Birkner, R. Richter, Carl Zeiss SMS GmbH (Germany)
- 7028 2X **IntenCD: mask critical dimension variation mapping** [7028-100]
A. Sagiv, N. Polonsky, O. Boiman, L. Shoval, M. Ben-Yishai, S. Mangan, Applied Materials (Israel)
- 7028 2Y **Registration measurement capability of VISTEC LMS IPRO4 with focus on small features** [7028-101]
C. Enkrich, G. Antesberger, O. Loeffler, Advanced Mask Technology Ctr. GmbH & Co. KG (Germany); K.-D. Roeth, F. Laske, K.-H. Schmidt, D. Adam, Vistec Semiconductor Systems GmbH (Germany)
- 7028 2Z **Phame: phase measurements on 45nm node phase shift features** [7028-102]
U. Buttgerit, R. Birkner, D. Seidel, S. Perltz, Carl Zeiss SMS GmbH (Germany); V. Philipsen, P. De Bisschop, IMEC (Belgium)
- 7028 30 **Influence of mask surface processing on CD-SEM imaging** [7028-103]
M. Hauptmann, Advanced Mask Technology Ctr. GmbH & Co. KG (Germany); L. M. Eng, Technische Univ. Dresden (Germany); J. Richter, Advanced Mask Technology Ctr. GmbH & Co. KG (Germany)
- 7028 31 **Finite element simulation of light propagation in non-periodic mask patterns** [7028-104]
L. Zschiedrich, F. Schmidt, Zuse Institute Berlin (Germany) and JCMwave GmbH (Germany)
- 7028 32 **PROVE: a photomask registration and overlay metrology system for the 45 nm node and beyond** [7028-105]
G. Klose, Carl Zeiss SMT AG (Germany); D. Beyer, Carl Zeiss SMS GmbH (Germany); M. Arnz, N. Kerwien, Carl Zeiss SMT AG (Germany); N. Rosenkranz, Carl Zeiss SMS GmbH (Germany)

POSTER SESSION 5G: MDP

- 7028 33 **Advanced mask data processing for 32nm and beyond** [7028-106]
J. Nogatch, D. Hung, R. Kondepudy, J. Yeap, Synopsys, Inc. (USA)
- 7028 34 **Comparison of verification methods for OASIS files: hierarchical or flat?** [7028-108]
K. Kato, Y. Taniguchi, M. Endo, K. Nishizawa, T. Inoue, T. Fujii, SII NanoTechnology Inc. (Japan)

POSTER SESSION 5H: EDA AND DFM

- 7028 35 **Utilization of design intent information for mask manufacturing** [7028-109]
K. Kato, M. Endo, T. Inoue, M. Yamabe, Association of Super-Advanced Electronics Technologies (Japan)

- 7028 36 **An extraction of repeating patterns from OPCed layout data** [7028-110]
F. Yoshihiro, M. Shoji, K. Kato, T. Inoue, M. Yamabe, Association of Super-Advanced Electronics Technologies (Japan)
- 7028 37 **Verification of mask manufacturing load estimation (MiLE)** [7028-111]
Y. Nagamura, Renesas Technology Corp. (Japan); S. Narukawa, Dai Nippon Printing Co., Ltd. (Japan); Y. Shika, H. Kabashima, A. Nakajo, I. Miyazaki, S. Aoyama, Renesas Technology Corp. (Japan); Y. Morikawa, H. Mohri, Dai Nippon Printing Co., Ltd. (Japan); T. Hatada, M. Kato, H. Kawase, Keirex Technology Inc. (Japan)
- 7028 38 **Evaluation of hotspot analysis flow using mask model** [7028-112]
S. Kawashima, K. Hayano, N. Kuwahara, S. Narukawa, Y. Morikawa, H. Mohri, N. Hayashi, Dai Nippon Printing Co., Ltd. (Japan)
- 7028 39 **Comparison of triple-patterning decomposition algorithms using aperiodic tiling patterns** [7028-113]
C. Cork, J.-C. Madre, Synopsys SARL (France); L. Barnes, Synopsys, Inc. (USA)
- 7028 3A **Electrical metrics for lithographic line-end tapering** [7028-114]
P. Gupta, Univ. of California, Los Angeles (USA); K. Jeong, A. B. Kahng, C.-H. Park, Univ. of California, San Diego (USA)

POSTER SESSION 5I: RET AND OPC

- 7028 3B **Modeling mask pellicle effects for OPC/RET** [7028-115]
L. Zavyalova, H. Song, K. Lucas, Q. Zhang, J. Shiely, Synopsys Inc. (USA)
- 7028 3D **A new approach to the DFM for the metals** [7028-118]
N.-Y. Chung, H.-S. Bae, B.-S. Seo, S.-H. Lee, S.-I. Kim, S.-Y. Lee, Samsung Electronics Co., Ltd. (South Korea)
- 7028 3E **Mask process effect aware OPC modeling** [7028-119]
K. Koo, S. Lee, J. Hwang, D. Beale, M. St. John, R. Lugg, S. Baek, M. Do, J. Choi, Synopsys, Inc. (USA); Y. Kim, M. Hong, Samsung Electronics Co., Ltd. (South Korea)
- 7028 3F **Mask shot count reduction strategies in the OPC flow** [7028-120]
J. Word, Mentor Graphics Corp. (USA); K. Mizuuchi, Mentor Graphics Japan (Japan); S. Fu, W. Brown, E. Sahouria, Mentor Graphics Corp. (USA)

POSTER SESSION 5J: LITHOGRAPHY TECHNOLOGIES

- 7028 3G **Application of super-diffraction-lithography (SDL) for advanced logic** [7028-121]
S. Nakao, S. Maejima, Renesas Technology (Japan); Y. Mitarai, Renesas Semiconductor Engineering (Japan); T. Hagiwara, S. Ogawa, T. Hanawa, K. Suko, Renesas Technology (Japan)
- 7028 3H **An IntenCD map of a reticle as a feed-forward input to DoseMapper** [7028-122]
M. Ben Yishai, Applied Materials (USA); J. Finders, R. Kazinczi, A. Bleeker, P. Luehrmann, I. Janssen, F. Duray, ASML (Netherlands); L. Shoval, C. Couderc, R. Piech, N. Hillel, I. Englard, Applied Materials (USA)

- 7028 3I **Tool-induced hotspot fixing flow for high volume products** [7028-123]
H. Mashita, T. Kotani, F. Nakajima, H. Mukai, K. Sato, S. Tanaka, K. Hashimoto, S. Inoue, Toshiba Corp. (Japan)
- 7028 3K **Dependence of mask topography effects on pattern variation under hyper-NA lithography** [7028-125]
A. Mimotogi, M. Itoh, S. Mimotogi, K. Sato, T. Sato, S. Tanaka, S. Inoue, Toshiba Corp. (Japan)
- 7028 3L **Optimization of mask absorber stacks and illumination settings for contact hole imaging** [7028-126]
A. Erdmann, T. Fühner, P. Evanschitzky, Fraunhofer-Institut of Integrated Systems and Device Technology (Germany)
- 7028 3M **Impact of illumination source symmetrization in OPC** [7028-127]
J. L. Sturtevant, L. Hong, S. Jayaram, Mentor Graphics Corp. (USA); S. P. Renwick, Nikon Precision (USA); M. McCallum, Nikon Precision Europe GmbH (United Kingdom); P. De Bisschop, IMEC (Belgium)

POSTER SESSION 5K: COST AND STRATEGY ON PHOTOMASK

- 7028 3N **Predicting lithography costs: guidance for ≤ 32 nm patterning solutions** [7028-128]
A. J. Hazelton, Nikon Corp. (Japan); A. Wüest, G. Hughes, M. Lercel, SEMATECH (USA)

Author Index

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